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(54) **MANUFACTURE OF COMPLEMENTARY MOS TRANSISTOR (CMOS)**

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(57) Abstract:

PURPOSE: To obtain a CMOS having enhanced characteristics by a simple process with a method, wherein high-concentration source and drain ion-implanted regions are respectively formed in an N-type well and a P-type well to heat-treat the source and drain ion-implanted regions.

CONSTITUTION: An N-type well 2 and a P-type well 3 are formed in a P-type silicon substrate 1 and thereafter, element isolation oxide films 4 are formed to form an operating region and an insulatingly isolated region. Subsequently, after buffer oxide films 5 are formed on the entire surface of the substrate 1, P-type impurity ions for controlling a threshold voltage are implanted in the entire surface of the substrate 1, including the operating region to form ion-implanted regions 6, and the regions 6 are heat-treated. Thereby, a low-concentration drain region of an N-channel MOSFET and pockets of a P-channel MOSFET can be formed without a masking process.

